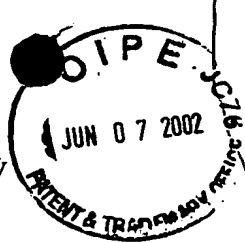


0039-7684-2SRD DIV



"RESPONSE UNDER 37 CFR 1.116-
EXPEDITED PROCEDURE EXAMINING
GROUP 2823"

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

HISAKO AOYAMA ET AL

: EXAMINER: MALDONADO, Julio J.

SERIAL NO: 09/558,053 :

FILED: APRIL 26, 2000

: GROUP ART UNIT: 2823

FOR: SEMICONDUCTOR DEVICE AND:
PROCESS OF FABRICATING THE
SAME

AMENDMENT UNDER 37 CFR §1.116

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office dated February 7, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claim 34 without prejudice.

Please amend the following claims as indicated in the attached marked-up copy:

29. (Thrice Amended) A process of fabricating a semiconductor device comprising

the steps of:

forming a first insulating film on a semiconductor substrate;

forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

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